

ABSTRACT OF THE DISCLOSURE

A method of forming an interlevel dielectric (ILD) layer forms a polymer sacrificial ILD on a substrate. After metallization structures are formed in the polymer sacrificial ILD layer, a low power etch back is performed on the sacrificial ILD layer. Dielectric material is non-conformally deposited as an ILD layer over the substrate and the metallization structures, forming air gaps between some of the metallization structures.